

IN THE CLAIMS:

Please CANCEL claims 1-10 without prejudice to or disclaimer of the recited subject matter.

Please ADD new claims 11-13, as follows. For the Examiner's convenience, all claims currently pending in this application have been reproduced below:

1-10. (Cancelled)

11. (New) A projection exposure apparatus having an exposure mode for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate, said apparatus comprising:

a light source for emitting an exposure beam; and

a projection optical system for receiving the exposure beam and for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate, wherein the mask includes (i) a substrate transparent for the exposure beam, and (ii) a member translucent for the exposure beam formed on the transparent substrate, the transmission factor of the translucent member being different from a transmission factor of the transparent substrate, wherein a difference between an optical path length of the exposure beam passing through the transparent substrate and the translucent member and an optical path length of the exposure beam passing through the transparent substrate and the space adjacent to the translucent member on the

transparent substrate is greater than $(m-1/8)\lambda$ and less than $(m+1/8)\lambda$, where λ is a wavelength of the exposure beam and m is an integer.

12. (New) A projection exposure apparatus having an exposure mode for exposing a reflection type mask to transfer a pattern image of the reflection type mask onto a photosensitive substrate, said apparatus comprising:

a light source for emitting an exposure beam; and

a projection optical system for receiving the exposure beam and for exposing a reflection type mask to transfer a pattern image of the reflection type mask onto a photosensitive substrate, wherein the reflection type mask includes (i) a substrate, and (ii) a reflective member having a reflection factor for the exposure beam formed on the substrate, the reflection factor being different from a reflection factor in a reflective area adjacent to the reflective member, wherein an optical path length difference between an exposure beam respectively reflecting in the reflective member and the reflective area is greater than $(m-1/8)\lambda$ and less than $(m+1/8)\lambda$, where λ is a wavelength of the exposure beam and m is an integer.

13. (New) An exposure apparatus having an exposure mode for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate, said apparatus comprising:

a light source for emitting an exposure beam; and

a projection optical system for receiving the exposure beam and for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate, wherein the mask

includes (i) a substrate transparent for the exposure beam, and (ii) a first member and a second member each translucent for the exposure beam and adjacent to each other, the transmission factors of the first and second members being different from each other, wherein a difference between an optical path length of an exposure beam passing through the transparent substrate and the first member and an optical path length of an exposure beam passing through the transparent substrate and the second member is greater than $(m-1/8)\lambda$ and less than $(m+1/8)\lambda$, where λ is a wavelength of the exposure beam and m is an integer.